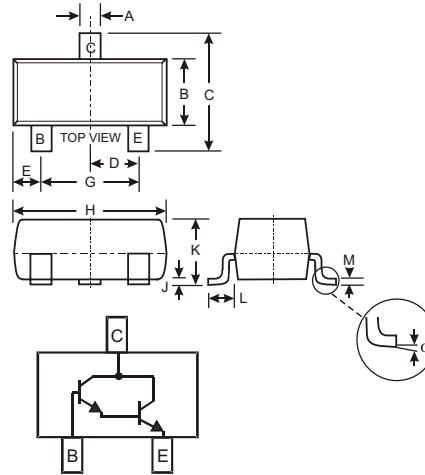


Features

- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- High Current Gain

Mechanical Data

- Case: SOT-23, Molded Plastic
- Case material - UL Flammability Rating Classification 94V-0
- Moisture sensitivity: Level 1 per J-STD-020A
- Terminals: Solderable per MIL-STD-202, Method 208
- Also Available in Lead Free Plating (Matte Tin Finish). Please see Ordering Information, Note 4, on Page 2
- Terminal Connections: See Diagram
- Marking (See Page 2): K1D
- Ordering & Date Code Information: See Page 2



SOT-23		
Dim	Min	Max
A	0.37	0.51
B	1.20	1.40
C	2.30	2.50
D	0.89	1.03
E	0.45	0.60
G	1.78	2.05
H	2.80	3.00
J	0.013	0.10
K	0.903	1.10
L	0.45	0.61
M	0.085	0.180
α	0°	8°
All Dimensions in mm		

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	MMBT6427	Unit
Collector-Base Voltage	V_{CB0}	40	V
Collector-Emitter Voltage	V_{CE0}	40	V
Emitter-Base Voltage	V_{EB0}	12	V
Collector Current - Continuous (Note 1)	I_C	500	mA
Power Dissipation (Note 1)	P_d	300	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Operating and Storage and Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 2)					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	40	—	V	$I_C = 100\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	40	—	V	$I_C = 100\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	12	—	V	$I_E = 10\mu\text{A}, I_C = 0$
Collector Cutoff Current	I_{CBO}	—	50	nA	$V_{CB} = 30\text{V}, I_E = 0$
Collector Cutoff Current	I_{CEO}	—	1.0	μA	$V_{CE} = 25\text{V}, I_B = 0$
Emitter Cutoff Current	I_{EBO}	—	50	nA	$V_{EB} = 10\text{V}, I_C = 0$
ON CHARACTERISTICS (Note 2)					
DC Current Gain	h_{FE}	10,000 20,000 14,000	100,000 200,000 140,000	—	$I_C = 10\text{mA}, V_{CE} = 5.0\text{V}$ $I_C = 100\text{mA}, V_{CE} = 5.0\text{V}$ $I_C = 500\text{mA}, V_{CE} = 5.0\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	1.2 1.5	V	$I_C = 50\text{mA}, I_B = 0.5\text{mA}$ $I_C = 500\text{mA}, I_B = 0.5\text{mA}$
Base- Emitter Saturation Voltage	$V_{BE(SAT)}$	—	2.0	V	$I_C = 500\text{mA}, I_B = 0.5\text{mA}$
Base- Emitter On Voltage	$V_{BE(ON)}$	—	1.75	V	$I_C = 50\text{mA}, V_{CE} = 5.0\text{V}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}	8.0 Typical		pF	$V_{CB} = 10\text{V}, f = 1.0\text{MHz}, I_E = 0$
Input Capacitance	C_{ibo}	15 Typical		pF	$V_{EB} = 0.5\text{V}, f = 1.0\text{MHz}, I_C = 0$

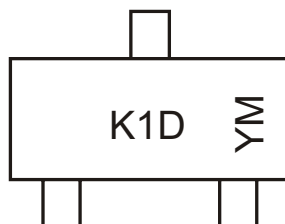
Note: 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
 2. Short duration test pulse used to minimize self-heating effect.

Ordering Information (Note 3)

Device	Packaging	Shipping
MMBT6427-7	SOT-23	3000/Tape & Reel

Notes: 3. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.
 4. For Lead Free version (with Lead Free terminal finish) part number, please add "-F" suffix to part number above.
 Example: MMBT6427-7-F.

Marking Information



K1D = Product Type Marking Code
 YM = Date Code Marking
 Y = Year ex: N = 2002
 M = Month ex: 9 = September

Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009
Code	J	K	L	M	N	P	R	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

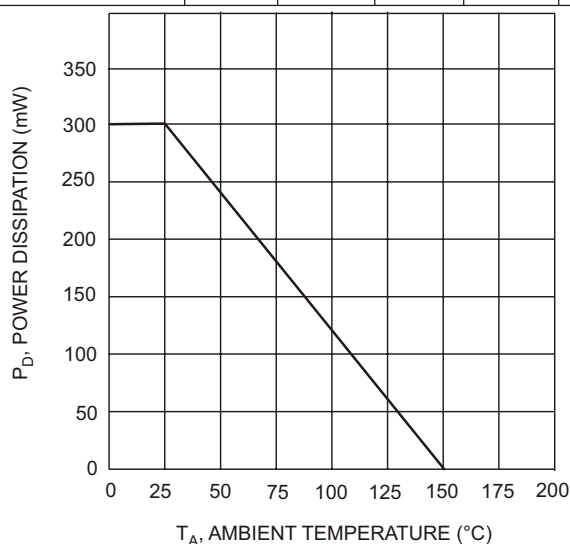


Fig. 1, Max Power Dissipation vs Ambient Temperature

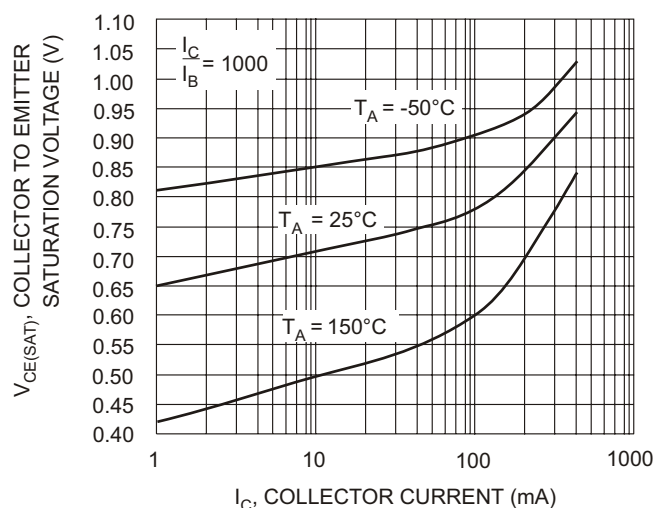


Fig. 2, Collector Emitter Saturation Voltage vs. Collector Current

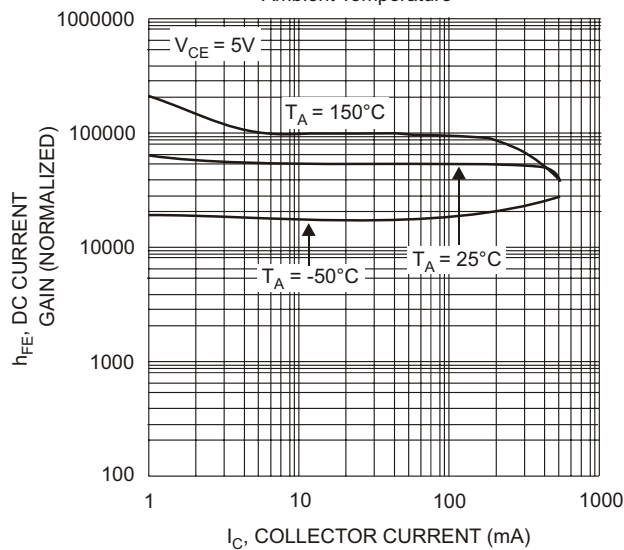


Fig. 3, DC Current Gain vs Collector Current

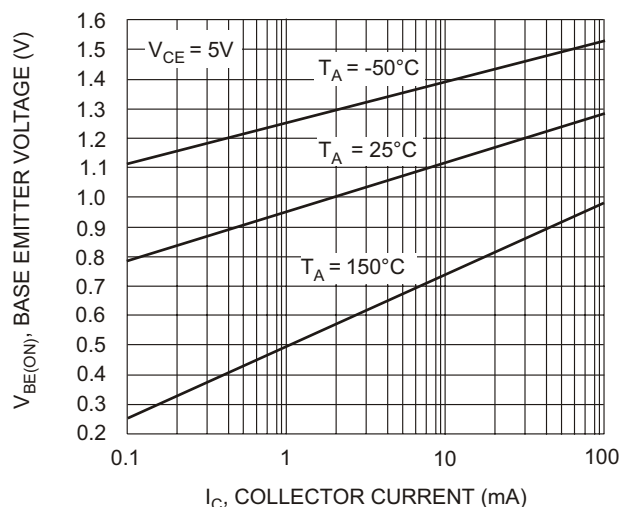


Fig. 4, Base Emitter Voltage vs. Collector Current

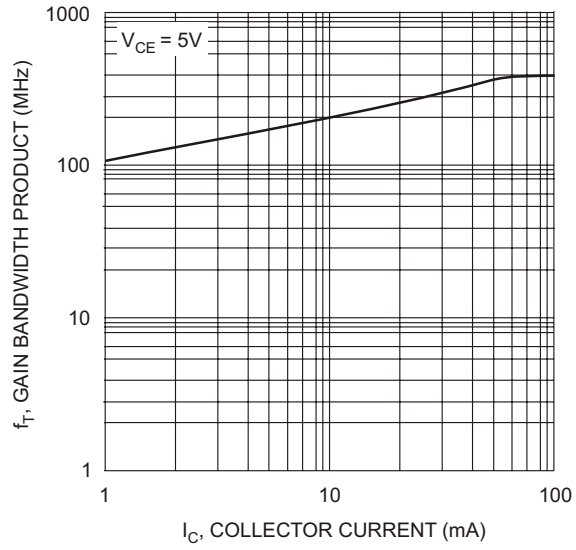


Fig. 5, Gain Bandwidth Product
vs Collector Current